

ABSTRACT OF THE DISCLOSURE

The active matrix substrate of the invention includes: a storage capacitor formed on a board; a first insulating layer formed on the storage capacitor; a semiconductor layer formed above the storage capacitor via the first insulating layer; a gate insulating layer formed on the semiconductor layer; a gate electrode layer including a gate electrode formed above the semiconductor layer via the gate insulating layer; a second insulating layer covering the gate electrode layer and the semiconductor layer; a first light-shielding layer formed above the semiconductor layer via the second insulating layer to cover at least a channel region of the semiconductor layer; a third insulating layer formed on the first light-shielding layer; a source electrode layer including source and drain electrodes formed on the third insulating layer; a fourth insulating layer formed on the source electrode layer; and a pixel electrode formed on the fourth insulating layer and electrically connected to the drain electrode. The first light-shielding layer is conductive and has a drain-side light-shielding portion electrically connected to one of a pair of electrodes of the storage capacitor and also to the drain electrode.